

## ABSTRACT

A method and system for preventing gas bubble formation on a selected region of a wafer surface as the surface is brought in contact with a process solution for an electrochemical process is provided. The present invention employs the process solution to prevent or remove gas bubbles from the wafer surface during or before the electrochemical processing of the wafer surface. Accordingly, during the process, the wafer surface is initially brought in proximity of the surface of the process solution. Next, a process solution flow is directed towards the selected region of the wafer surface for a predetermined time. In the following step, the selected region of the wafer surface is contacted with the process solution flow for the predetermined time to prevent bubble formation, and the wafer surface is immersed into the process solution for electrochemical processing.